

# MA4X193

## Silicon epitaxial planar type

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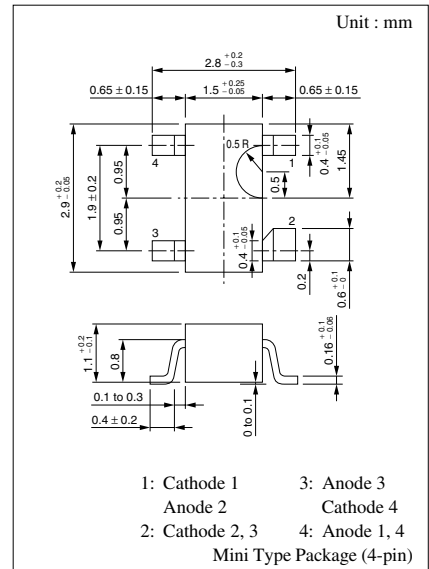
### ■ Features

- Mini type 4-pin package, contained four elements
- Short reverse recovery time  $t_{rr}$
- Bridge diodes for surface mounting
- Anode common + cathode common composite product

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

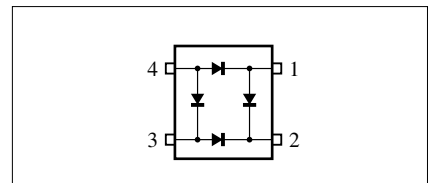
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	80	V
Repetitive peak reverse voltage	$V_{RRM}$	80	V
Average forward current	$I_{F(AV)}$	70	mA
Repetitive peak forward current	$I_{FRM}$	150	mA
Non-repetitive peak forward surge current*	$I_{FSM}$	250	mA
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \* :  $t = 1 \text{ s}$



Marking Symbol: M2Z

Internal Connection

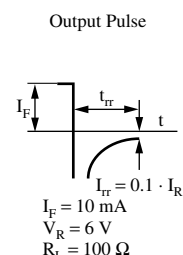
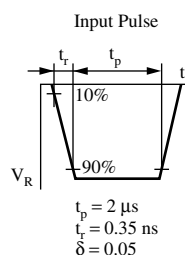
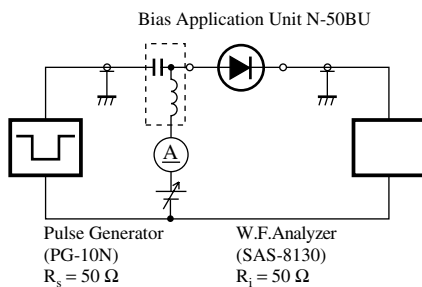


### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

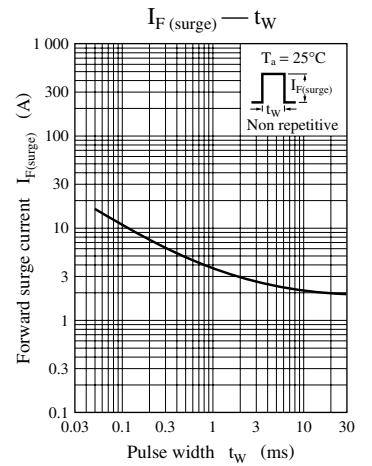
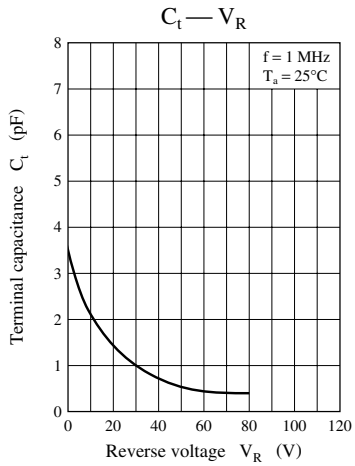
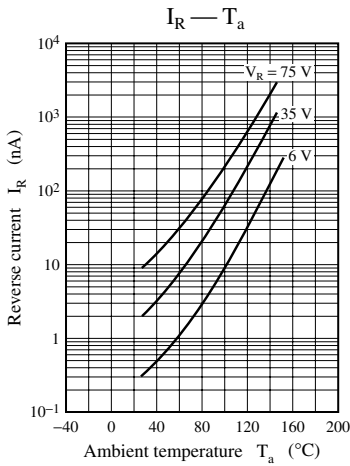
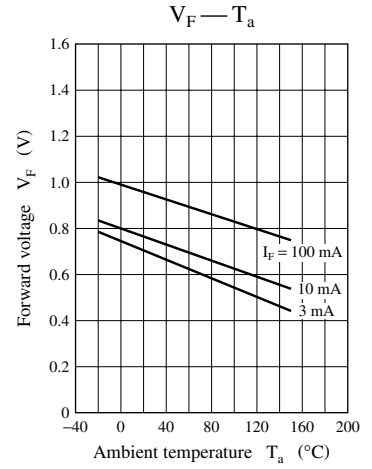
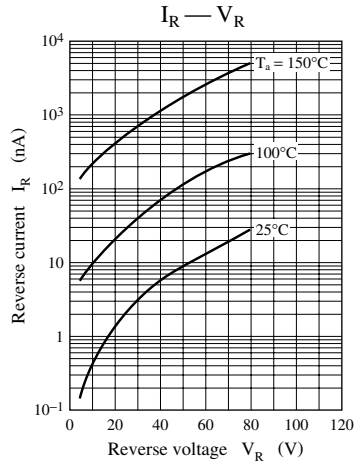
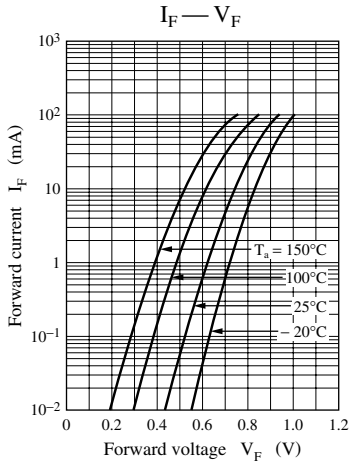
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 75 \text{ V}$			100	nA
Forward voltage (DC)	$V_F$	$I_F = 70 \text{ mA}$			1.2	V
Reverse voltage (DC)	$V_R$	$I_R = 100 \mu\text{A}$	80			V
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			15	pF
Reverse recovery time*	$t_{rr}$	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{tr} = 0.1 \cdot I_R, R_L = 100 \Omega$			10	ns

Note) 1. Rated input/output frequency: 100 MHz

2. \* :  $t_{rr}$  measuring circuit



4-1 and 4-3 pins (anode common) characteristics charts



1-2 and 3-2 pins (cathode common) characteristics charts

